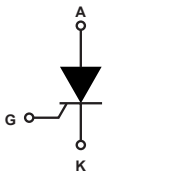
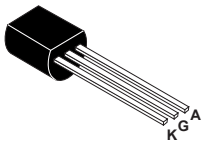
P0109DA

Datasheet

0.8 A 400 V high immunity sensitive SCR thyristor in TO-92





TO-92

Features

- On-state rms current, $I_{T(RMS)}$ 0.8 A
- 125 °C max. T_j
- Ultra low 1 µA gate current
- Repetitive peak off-state voltage, $V_{DRM/VRRM}$ 400 V
- ECOPACK2 compliant

Applications

- Gate driver for large Thyristors
- Overvoltage crowbar protection
- Ground fault circuit interrupters
- Arc fault circuit interrupter
- Standby mode power supplies
- Residual current detector

Description

Thanks to highly sensitive triggering levels, the 0.8 A P0109DA SCR thyristor is suitable for all applications where available gate current is limited.

This device offers a high blocking voltage of 400 V, ideal for applications like interrupters circuits.

The P0109DA is available in through-hole TO-92 package.

Product status link
P0109DA

Product summary	
$I_{T(RMS)}$	0.8 A
V_{DRM}/V_{RRM}	400 V
I_{GT}	1 µA
$T_j$max.	125 °C

1 Characteristics

Table 1. Absolute maximum ratings (limiting values)

Symbol	Parameters			Value	Unit
$I_{T(RMS)}$	On-state RMS current (180° conduction angle)		T_L = 55 °C	0.8	A
$I_{T(AV)}$	Average on-state current (180° conduction angle)			0.5	A
I_{TSM}	Non repetitive surge peak on-state current, T_j initial = 25 °C	t_p = 8.3 ms	T_j = 25 °C	8	A
		t_p = 10 ms		7	
I^2t	I^2t value for fusing	t_p = 10 ms	T_j = 25 °C	0.24	A^2s
dI/dt	Critical rate of rise of on-state current I_G = 2 x I_{GT} , $t_r \leq$ 100 ns	F = 60 Hz	T_j = 25 °C	50	A/µs
V_{DRM} / V_{RRM}	Repetitive peak off-state voltage		T_j = 125 °C	400	V
I_{GM}	Peak gate current	t_p = 20 µs	T_j = 125 °C	1	A
$P_{G(AV)}$	Average gate power dissipation		T_j = 125 °C	0.1	W
T_{stg}	Storage junction temperature range			-40 to +150	°C
T_j	Operating junction temperature range			-40 to +125	°C

Table 2. Electrical characteristics (T_j = 25 °C, unless otherwise specified)

Symbol	Parameters		Value	Unit
I_{GT}	V_D = 12 V, R_L = 33 Ω	Max.	1	µA
V_{GT}		Max.	0.8	V
V_{GD}	V_D = V_{DRM}, R_L = 3.3 kΩ, R_{GK} = 1 kΩ, T_j = 125 °C	Min.	0.1	V
V_{RG}	I_{RG} = 10 µA	Min.	8	
I_H	I_T = 50 mA, R_{GK} = 1 kΩ	Max.	5	mA
I_L	I_G = 1.2 I_{GT}, R_{GK} = 1 kΩ	Max.	6	mA
dV/dt	V_D = 67 % V_{DRM}, R_{GK} = 1 kΩ, T_j = 125 °C	Min.	75	V/µs

Table 3. Static electrical characteristics

Symbol	Test conditions	T_j		Value	Unit
V_T	I_{TM} = 1.6 A, t_p = 380 µs	25 °C	Max.	1.95	V
V_{TO}	Threshold on-state voltage	125 °C	Max.	0.95	V
R_d	Dynamic resistance	125 °C	Max.	600	mΩ
I_{DRM}	V_D = V_{DRM}	25 °C	Max.	1	µA
I_{RRM}	V_R = V_{RRM}	125 °C		0.1	mA

Table 4. Thermal resistance

Symbol	Parameters	Max. value	Unit
$R_{th(j-l)}$	Junction to lead (DC)	80	°C/W
$R_{th(j-a)}$	Junction to ambient (DC)	150	

1.1 Characteristics (curves)

Figure 1. Maximum power dissipation versus on-state RMS current (full cycle)

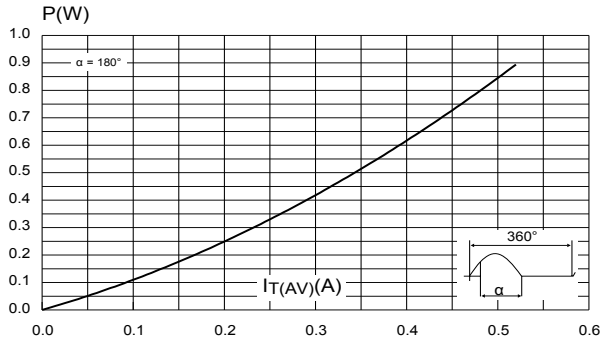


Figure 2. Average and DC on-state current versus lead temperature

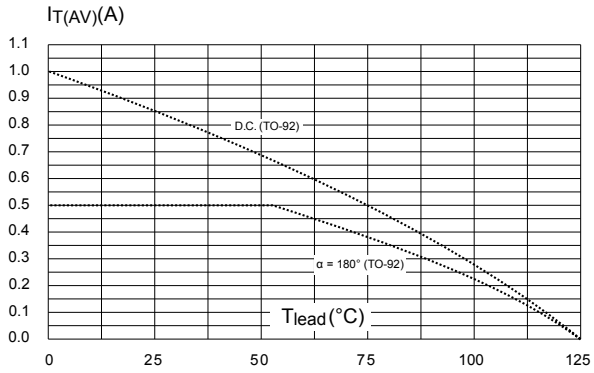


Figure 3. Average and DC on-state current versus ambient temperature

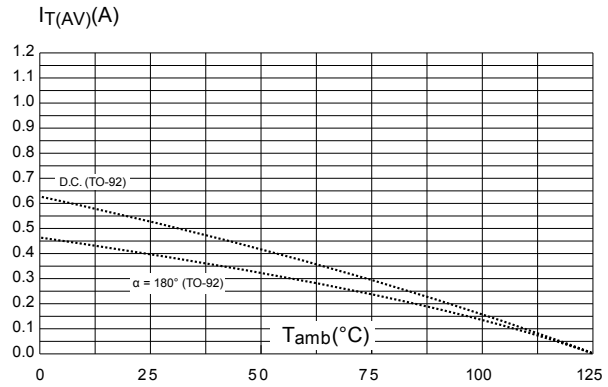


Figure 4. Relative variation of thermal impedance versus pulse duration

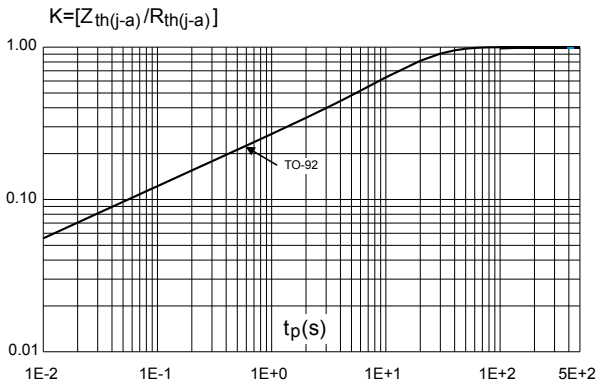


Figure 5. Relative variation of holding current versus gate-cathode resistance

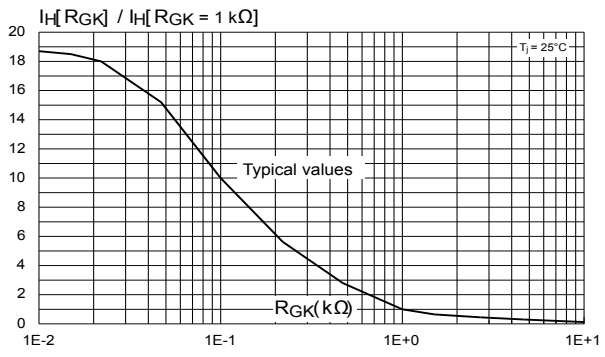


Figure 6. Relative variation of gate voltage and gate, holding and latching current versus junction temperature

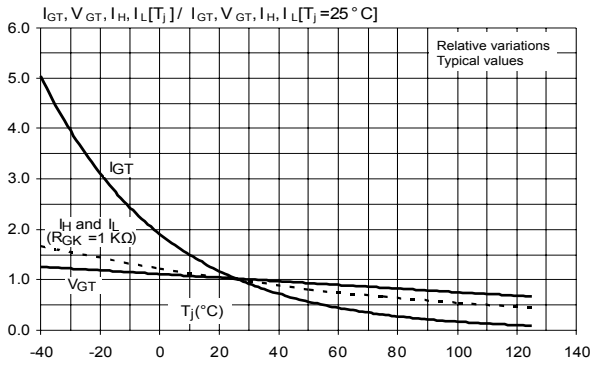


Figure 7. Relative variation of static dV/dt immunity versus gate-cathode resistance

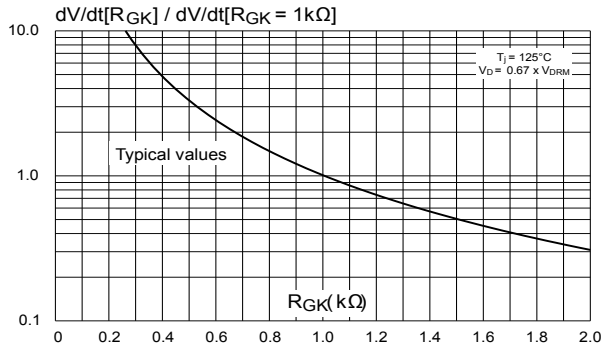


Figure 8. Relative variation of dV/dt immunity versus gate-cathode capacitance

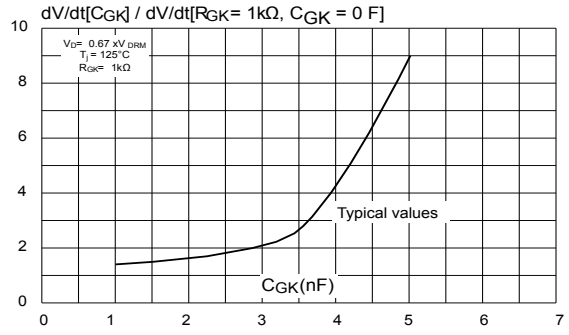


Figure 9. Surge peak on-state current versus number of cycles

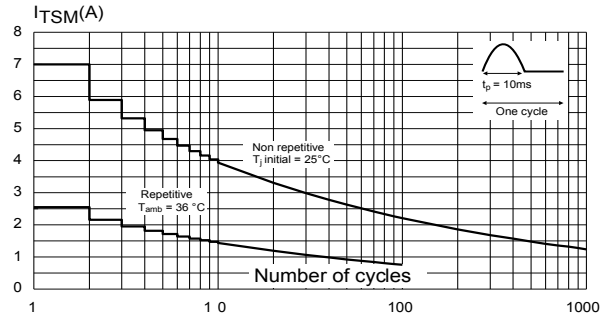


Figure 10. Non-repetitive surge peak on-state current for sinusoidal pulse (t_p< 10 ms)

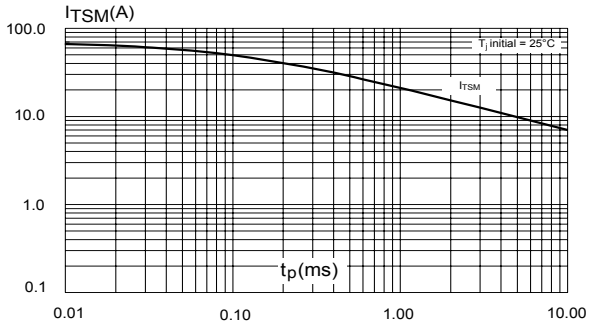
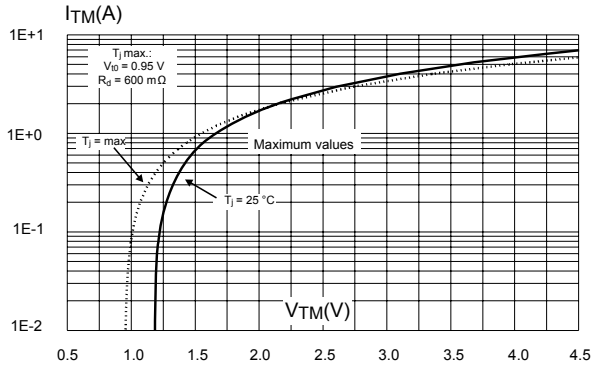


Figure 11. On-state characteristics (maximum values)



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 TO-92 package information

- Lead free plating + halogen-free molding resin
- Epoxy meets UL94, V0

Figure 12. TO-92 package outline

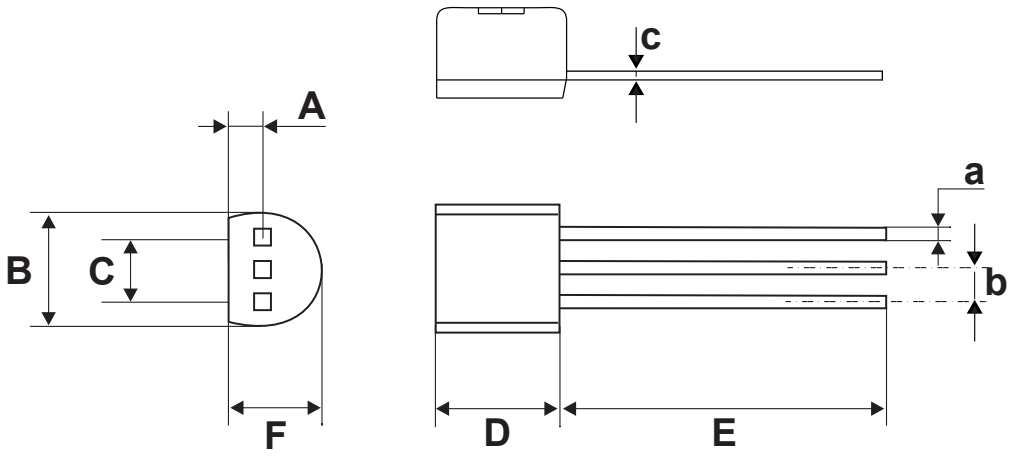


Table 5. TO-92 package mechanical data

Ref.	Dimensions					
	Millimeters			Inches(1)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		1.35			0.0531	
B			4.70			0.1850
C		2.54			0.1000	
D	4.40			0.1732		
E	12.70			0.5000		
F			3.70			0.1457
a			0.50			0.0197
b		1.27			0.0500	
c			0.48			0.0189

1. *Inches dimensions given for information*

3 Ordering information

Figure 13. **Ordering information scheme**

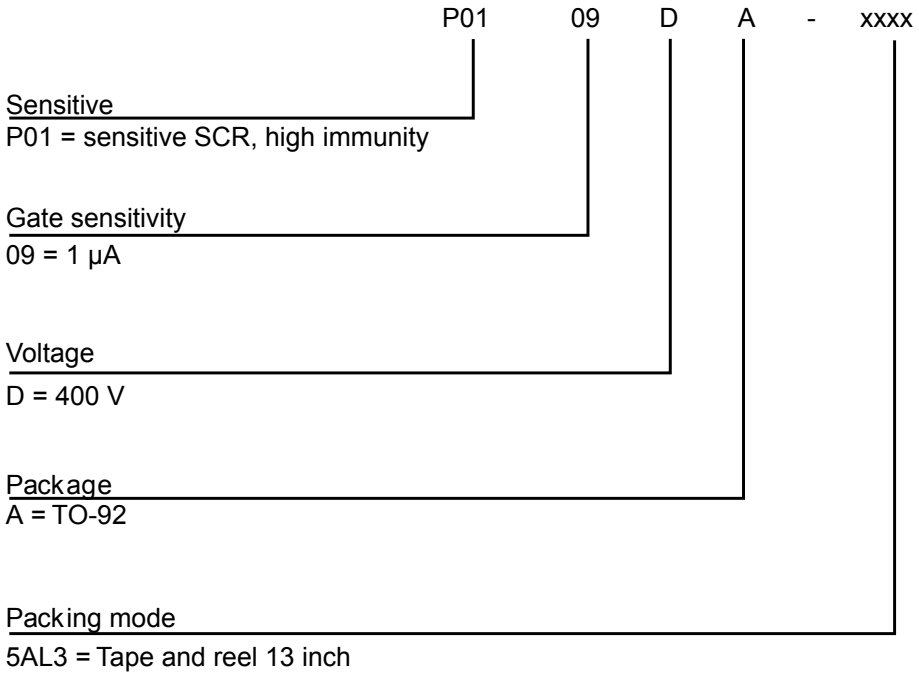


Table 6. **Ordering information**

Order code	Marking	Package	Weight	Base qty.	Delivery mode
P0109DA 5AL3	P0109 DA	TO-92	0.22 g	2000	Tape and reel 13"

Revision history

Table 7. **Document revision history**

Date	Revision	Changes
20-Jan-2020	1	Initial release.
16-Jun-2020	2	Updated Section Cover image.

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